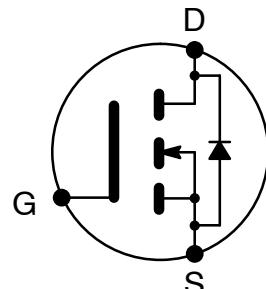


NTE2922
MOSFET
N-Ch, Enhancement Mode
High Speed Switch
TO3P Type Package

Features:

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Parallelizing
- Simple Drive Requirements



Absolute Maximum Ratings:

Continuous Drain Current ($V_{GS} = 10V$), I_D	
$T_C = +25^\circ C$	16A
$T_C = +100^\circ C$	10A
Pulsed Drain Current (Note 1), I_{DM}	64A
Power Dissipation ($T_C = +25^\circ C$), P_D	180W
Gate-to-Source Voltage, V_{GS}	± 20
Single Pulse Avalanche Energy (Note 2), E_{AS}	390mJ
Avalanche Current (Note 1), I_{AR}	16A
Repetitive Avalanche Energy (Note 1), E_{AR}	19mJ
Peak Diode Recovery dv/dt (Note 3), dv/dt	4V/ns
Operating Junction Temperature Range, T_J	-55° to +150°C
Storage Temperature Range, T_{stg}	-55° to +150°C
Lead Temperature (During Soldering, 1.6mm from case for 10sec), T_L	+300°C
Thermal Resistance, Junction-to-Case, R_{thJC}	0.7°C/W
Thermal Resistance, Junction-to-Ambient, R_{thJA}	30°C/W

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 2. $V_{DD} = 50V$, starting $T_J = +25^\circ C$, $L = 2.7mH$, $R_G = 25\Omega$, $I_{AS} = 16A$

Note 3. $I_{SD} \leq 16A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq 400V$, $T_J \leq +150^\circ C$

Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	400	—	—	V
Breakdown Voltage Temp. Coefficient	$\frac{\Delta V_{(\text{BR})\text{DSS}}}{\Delta T_J}$	Reference to $+25^\circ\text{C}$, $I_D = 1\text{mA}$	—	0.51	—	$\text{V}/^\circ\text{C}$
Static Drain-to-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 8.9\text{A}$	—	—	0.30	Ω
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	—	4.0	V
Forward Transconductance	g_{fs}	$V_{\text{DS}} = 40\text{V}, I_D = 8\text{A}$	8	—	—	S
Drain-to-Source Leakage Current	I_{DSS}	$V_{\text{DS}} = 400\text{V}, V_{\text{GS}} = 0\text{V}$	—	—	25	μA
Gate-to-Source Forward Leakage	I_{GSS}	$V_{\text{GS}} = 20\text{V}, V_{\text{DS}} = 0$	—	—	100	nA
Gate-to-Source Reverse Leakage	I_{GSR}	$V_{\text{GS}} = -20\text{V}, V_{\text{DS}} = 0$	—	—	-100	nA
Total Gate Charge	Q_g	$I_D = 16\text{A}, V_{\text{DS}} = 320\text{V}, V_{\text{GS}} = 10\text{V}$, Note 4	—	—	150	nC
Gate-to-Source Charge	Q_{gs}		—	—	23	nC
Gate-to-Drain ("Miller") Charge	Q_{gd}		—	—	80	nC
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 200\text{V}, I_D = 16\text{A}, R_G = 6.2\Omega$, $R_D = 12\Omega$, Note 4	—	16	—	ns
Rise Time	t_r		—	49	—	ns
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		—	87	—	ns
Fall Time	t_f		—	47	—	ns
Internal Drain Inductance	L_D	Between lead, .250in. (6.0) mm from package and center of die contact	—	5.0	—	nH
Internal Source Inductance	L_S		—	13	—	nH
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1\text{MHz}$	—	2600	—	pF
Output Capacitance	C_{oss}		—	660	—	pF
Reverse Transfer Capacitance	C_{rss}		—	250	—	pF

Source-Drain Ratings and Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Source Current (Body Diode)	I_S		—	—	16	A
Pulsed Source Current (Body Diode)	I_{SM}	Note 1	—	—	64	A
Diode Forward Voltage	V_{SD}	$T_J = +25^\circ\text{C}, I_S = 16\text{A}, V_{\text{GS}} = 0\text{V}$	—	—	1.6	V
Reverse Recovery Time	t_{rr}	$T_J = +25^\circ\text{C}, I_F = 16\text{A}$, $dI/dt = 100\text{A}/\mu\text{s}$, Note 4	—	380	570	ns
Reverse Recovery Charge	Q_{rr}		—	4.7	7.1	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 4. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

